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10/15/03
MD

In The Claims

1. (currently amended): A method of forming uniform metal nitrides (MN) comprising contacting heated metal with flowing iodine (I_2) vapor, at pressures below 760 Torr, to form a metal iodide (MI) and then contacting flowing said MI into contact with ammonia, at pressures below 760 Torr, to form said MN.
2. (original): The method of claim 1 conducted in a reactor wherein the reactor pressure is maintained between 750 and 75 Torr.
3. (original): The method of claim 1 wherein said reduced pressures are between 600-100 Torr.
4. (original): The method of claim 1 wherein said reduced pressures are between 100-5 Torr.
5. (original): The method of claim 1 wherein said M is gallium, aluminum, indium or alloys thereof.
6. (original): The method of claim 1 wherein said MN is gallium nitride (GaN), aluminum nitride (AlN), indium nitride (InN) and ternary and quaternary nitrides such as gallium aluminum nitride (GaAlN), gallium arsenic nitride (GaAsN), gallium aluminum indium nitride (GaAlInN) or gallium arsenic indium nitride (GaAsInN).
7. (original): The method of claim 1 wherein said MI is formed in one locale and then is flowed to another locale to react with ammonia to form said MN.
8. (previously presented): The method of claim 1 wherein said MN is formed as a vapor and deposited on a seed or self-nucleates on a nearby surface.
9. (previously presented): The method of claim 1 wherein